

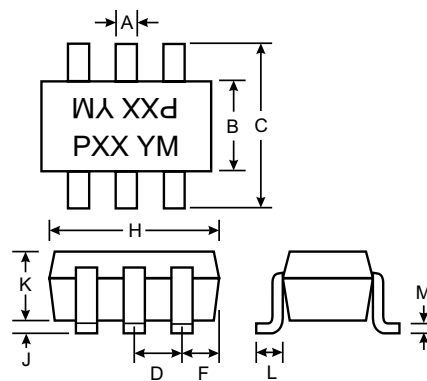
### Features

- Epitaxial Planar Die Construction
- Complementary NPN Types Available (DDC)
- Built-In Biasing Resistors

### Mechanical Data

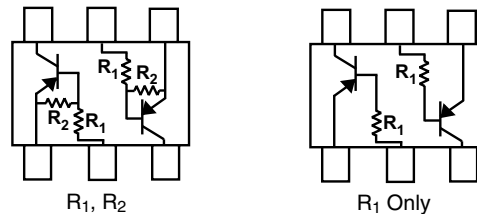
- Case: SOT-363, Molded Plastic
- Case material - UL Flammability Rating 94V-0
- Terminals: Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Weight: 0.006 grams (approx.)

UNDER DEVELOPMENT



SOT-363		
Dim	Min	Max
A	0.10	0.30
B	1.15	1.35
C	2.00	2.20
D	0.65 Nominal	
E	0.30	0.40
G	1.80	2.20
H	1.80	2.20
J	—	0.10
K	0.90	1.00
L	0.25	0.40
M	0.10	0.25
All Dimensions in mm		

P/N	R1	R2	MARKING
DDA124EU	22K	22K	P17
DDA144EU	47K	47K	P20
DDA114YU	10K	47K	P14
DDA123JU	2.2K	47K	P06
DDA114EU	10K	10K	P13
DDA143TU	4.7K	-	P07
DDA114TU	10K	-	P12



SCHEMATIC DIAGRAM

### Maximum Ratings @ T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Supply Voltage, (3) to (1)	V <sub>CC</sub>	50	V
Input Voltage, (2) to (1)	V <sub>IN</sub>	+10 to -40 +10 to -40 +6 to -40 +5 to -12 +10 to -40 +5 V <sub>max</sub> +5 V <sub>max</sub>	V
Output Current	I <sub>O</sub>	-30 -30 -70 -100 -50 -100 -100	mA
Output Current	I <sub>C</sub> (Max)	-100	mA
Power Dissipation	P <sub>d</sub>	-200	mW
Operating and Storage and Temperature Range	T <sub>j</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics** @ T<sub>A</sub> = 25°C unless otherwise specified

Characteristic (DDA143TU & DDA114TU only)	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	-50	—	—	V	I <sub>C</sub> = -50μA
Collector-Emitter Breakdown Voltage	BV <sub>CEO</sub>	-50	—	—	V	I <sub>C</sub> = -1mA
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	-5	—	—	V	I <sub>E</sub> = -50μA
Collector Cutoff Current	I <sub>CBO</sub>	—	—	-0.5	μA	V <sub>CB</sub> = -50V
Emitter Cutoff Current	I <sub>EBO</sub>	—	—	-0.5	μA	V <sub>EB</sub> = -4V
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	—	—	-0.3	V	I <sub>C</sub> /I <sub>B</sub> = -2.5mA / -0.25mA I <sub>C</sub> /I <sub>B</sub> = -1mA / -0.1mA DDA143TU DDA114TU
DC Current Transfer Ratio	h <sub>FE</sub>	100	250	600	—	I <sub>C</sub> = -1mA, V <sub>CE</sub> = -5V
Gain-Bandwidth Product*	f <sub>T</sub>	—	250	—	MHz	V <sub>CE</sub> = -10V, I <sub>E</sub> = 5mA, f = 100MHz

Characteristic		Symbol	Min	Typ	Max	Unit	Test Condition
Input Voltage	DDA124EU DDA144EU DDA114YU DDA123JU DDA114EU	V <sub>I(off)</sub>	-0.5 -0.5 -0.3 -0.5 -0.5	-1.1 -1.1 — — -1.1	—	V	V <sub>CC</sub> = -5V, I <sub>O</sub> = -100μA
	DDA124EU DDA144EU DDA114YU DDA123JU DDA114EU	V <sub>I(on)</sub>	—	— — — -1.9	-1.9 -1.9 -1.4 -1.1 -3.0		
Output Voltage	DDA124EU DDA144EU DDA114YU DDA123JU DDA114EU	V <sub>O(on)</sub>	—	-0.1	-0.3	V	I <sub>O</sub> /I <sub>I</sub> = -10mA / -0.5mA I <sub>O</sub> /I <sub>I</sub> = -10mA / -0.5mA I <sub>O</sub> /I <sub>I</sub> = -5mA / -0.25mA I <sub>O</sub> /I <sub>I</sub> = -5mA / -0.25mA I <sub>O</sub> /I <sub>I</sub> = -10mA / -0.5mA
Input Current	DDA124EU DDA144EU DDA114YU DDA123JU DDA114EU	I <sub>I</sub>	—	—	-0.36 -0.18 -0.88 -3.6 -0.88	mA	V <sub>I</sub> = -5V
Output Current		I <sub>O(off)</sub>	—	—	-0.5	μA	V <sub>CC</sub> = -50V, V <sub>I</sub> = -0V
DC Current Gain	DDA124EU DDA144EU DDA114YU DDA123JU DDA114EU	G <sub>I</sub>	56 68 68 80 30	—	—	—	V <sub>O</sub> = -5V, I <sub>O</sub> = -5mA V <sub>O</sub> = -5V, I <sub>O</sub> = -5mA V <sub>O</sub> = -5V, I <sub>O</sub> = -10mA V <sub>O</sub> = -5V, I <sub>O</sub> = -10mA V <sub>O</sub> = -5V, I <sub>O</sub> = -5mA
Gain-Bandwidth Product*		f <sub>T</sub>	—	250	—	MHz	V <sub>CE</sub> = -10V, I <sub>E</sub> = -5mA, f = 100MHz

\* Transistor - For Reference Only

UNDER DEVELOPMENT